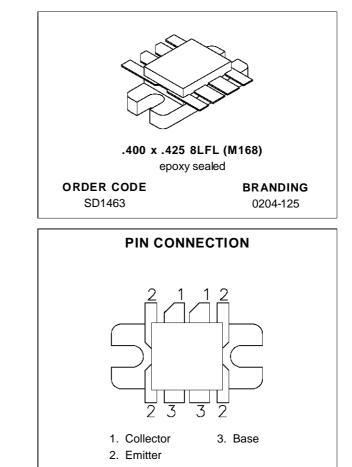


# ICS (TCC0204-125) RF & MICROWAVE TRANSISTORS VHF/UHF APPLICATIONS

**SD1463** 

- 400 MHz
- 28 VOLTS
- EFFICIENCY 60%
- COMMON EMITTER
- GOLD METALLIZATION
- POUT = 125 W MIN. WITH 7.0 dB GAIN



## DESCRIPTION

The SD1463 is a 28 V Class C gold metallized epitaxial silicon NPN planar transistor designed for UHF military and commercial equipment. The SD1463 is an internally matched, broadband device optimized for operation within the 225 - 400 MHz frequency range. This device utilizies diffused emitter resistors to achieve 10:1 VSWR load mismatch capability at rated operating conditions.

## **ABSOLUTE MAXIMUM RATINGS** $(T_{case} = 25^{\circ}C)$

Symbol	Parameter	Value	Unit
Vсво	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
Ι <sub>C</sub>	Device Current	15	A
P <sub>DISS</sub>	Power Dissipation	270	W
TJ	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	– 65 to +150	°C

#### THERMAL DATA

R <sub>TH(j-c)</sub> Junction-Case Thermal Resistance	0.65	°C/W
---	------	------

# **ELECTRICAL SPECIFICATIONS** ( $T_{case} = 25^{\circ}C$ )

## STATIC

Symbol	Symbol Test Conditions		Value			Unit	
Symbol				Min.	Тур.	Max.	Unit
ВVсво	I <sub>C</sub> = 100 mA	$I_E = 0 \text{ mA}$		60	_	-	V
BVCES	I <sub>C</sub> = 80 mA	$V_{BE} = 0 V$		60	—	_	V
BV <sub>CEO</sub>	$I_C = 50 \text{ mA}$	$I_B = 0 \text{ mA}$		30	_		V
BV <sub>EBO</sub>	$I_E = 20 \text{ mA}$	$I_{C} = 0 \text{ mA}$		4.0	_		V
I <sub>CBO</sub>	$V_{CB} = 30 V$	$I_E = 0 mA$		_	_	10	mA
hFE	$V_{CE} = 5 V$	I <sub>C</sub> = 1 A		20	_	200	_

# DYNAMIC

Symbol	Symbol Test Conditions				Value		
Symbol		Test conditions		Min.	Тур.	Max.	Unit
PIN	f = 400 MHz	$P_{OUT} = 125 W$	$V_{CC} = 28 V$	—		25	W
GP	f = 400 MHz	$P_{OUT} = 125 W$	$V_{CC} = 28 V$	7.0			dB
ης	f = 400 MHz	$P_{OUT} = 125 W$	$V_{CC} = 28 V$	60			%

# IMPEDANCE DATA

FREQ.	Z <sub>IN</sub> (Ω)	Z <sub>CL</sub> (Ω)
225 MHz	0.5 + j 2.5	8.8 + j 3.5
400 MHz	1.5 + j 1.7	5.0 + j 0.0



## PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0168 rev. A UDCS Doc. No. 1010993						
	* !					
	SGS-THOMSON MIC	RUELECTRUNICS		CD)	מידא	]
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm	
A	.D3	0/0,76	к	.003/0,08	.007/0,18	]
В	.115/2,92	.125/3,18	L	.120/3,05	130/3,30	
c	.36	0/9,14	м	.159/4,04	.175/4,45	]
a	.065/1,65	.075/1,91	N		.280/7,11	1
E	13	0/3,30	0	.395/10,03	.405/10,29	
F	.380/9,65	.390/9,91				]
۵	.735/18,67	.765/19,43	]			-
н	.645/16,38	.655/16,64	]			
I	.895/22,73	.905/22,99	]			
L	.420/10,67	430/10,92	]			
			-			

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

©1996 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia -Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan -Thailand - United Kingdom - U.S.A.



This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.